

V_{DSS}	1200V
$R_{DS(on)}$ (Typ.)	280mΩ
I_D	14A
P_D	108W

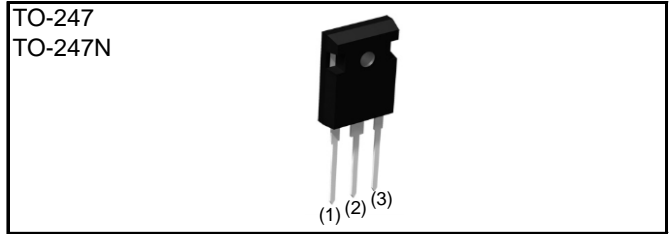
●Features

- 1) Low on-resistance
- 2) Fast switching speed
- 3) Fast reverse recovery
- 4) Easy to parallel
- 5) Simple to drive
- 6) Pb-free lead plating ; RoHS compliant

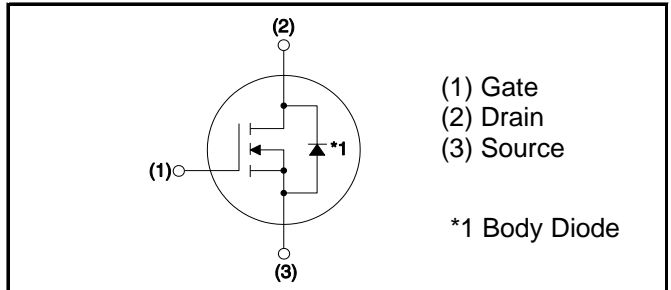
●Application

- Solar inverters
- DC/DC converters
- Induction heating
- Motor drives

●Outline



●Inner circuit



●Packaging specifications^{*1}

Package		TO-247	TO-247N
Type	Packing	Tube	
	Reel size (mm)	-	
	Tape width (mm)	-	
	Basic ordering unit (pcs)	30	
	Packing code	C	C11
	Marking	SCT2280KE	

●Absolute maximum ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Drain - Source voltage	V_{DSS}	1200	V
Continuous drain current	$T_c = 25^\circ\text{C}$	I_D^{*2} 14	A
	$T_c = 100^\circ\text{C}$	I_D^{*2} 10	A
Pulsed drain current	$I_{D,pulse}^{*3}$	35	A
Gate - Source voltage (DC)	V_{GSS}	-6 to 22	V
Gate - Source surge voltage ($T_{surge} < 300\text{nsec}$)	$V_{GSS-surge}^{*4}$	-10 to 26	V
Power dissipation ($T_c = 25^\circ\text{C}$)	P_D	108	W
Junction temperature	T_j	175	$^\circ\text{C}$
Range of storage temperature	T_{stg}	-55 to +175	$^\circ\text{C}$

●Electrical characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain - Source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 1mA	1200	-	-	V
Zero gate voltage drain current	I _{DSS}	V _{DS} = 1200V, V _{GS} = 0V T _j = 25°C	-	1	10	μA
			-	2	-	
Gate - Source leakage current	I _{GSS+}	V _{GS} = +22V, V _{DS} = 0V	-	-	100	nA
Gate - Source leakage current	I _{GSS-}	V _{GS} = -6V, V _{DS} = 0V	-	-	-100	nA
Gate threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 1.4mA	1.6	2.8	4.0	V

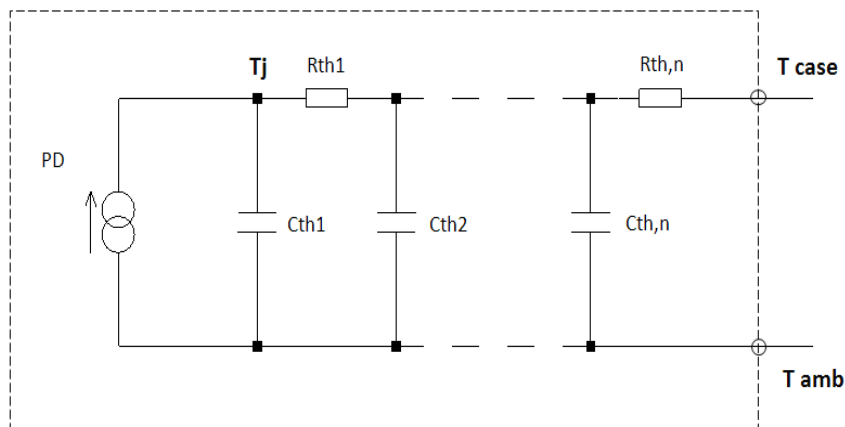
●Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction - case	R _{thJC}	-	1.07	1.39	°C/W
Thermal resistance, junction - ambient	R _{thJA}	-	-	50	°C/W
Soldering temperature, wavesoldering for 10s	T _{sold}	-	-	265	°C

●Typical Transient Thermal Characteristics

Symbol	Value	Unit
R _{th1}	1.00E-01	K/W
R _{th2}	6.62E-01	
R _{th3}	3.04E-01	

Symbol	Value	Unit
C _{th1}	8.61E-04	Ws/K
C _{th2}	2.84E-03	
C _{th3}	5.59E-02	



●Electrical characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Static drain - source on - state resistance	R _{DS(on)} ^{*5}	V _{GS} = 18V, I _D = 4A	-	280	364	mΩ
		T _j = 25°C	-	388	-	
Gate input resistance	R _G	f = 1MHz, open drain	-	17	-	Ω
Transconductance	g _{fs} ^{*5}	V _{DS} = 10V, I _D = 4A	-	1.4	-	S
Input capacitance	C _{iss}	V _{GS} = 0V	-	667	-	pF
Output capacitance	C _{oss}	V _{DS} = 800V	-	27	-	
Reverse transfer capacitance	C _{rss}	f = 1MHz	-	5	-	
Effective output capacitance, energy related	C _{o(er)}	V _{GS} = 0V V _{DS} = 0V to 500V	-	41	-	pF
Turn - on delay time	t _{d(on)} ^{*5}	V _{DD} = 400V, V _{GS} = 18V	-	19	-	ns
Rise time	t _r ^{*5}	I _D = 4A	-	19	-	
Turn - off delay time	t _{d(off)} ^{*5}	R _L = 100Ω	-	47	-	
Fall time	t _f ^{*5}	R _G = 0Ω	-	29	-	
Turn - on switching loss	E _{on} ^{*5}	V _{DD} = 600V, I _D =4A V _{GS} = 18V/0V	-	57	-	μJ
Turn - off switching loss	E _{off} ^{*5}	R _G = 0Ω, L=500μH *E _{on} includes diode reverse recovery	-	20	-	

●Gate Charge characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Total gate charge	Q _g ^{*5}	V _{DD} = 400V	-	36	-	nC
Gate - Source charge	Q _{gs} ^{*5}	I _D = 4A	-	9	-	
Gate - Drain charge	Q _{gd} ^{*5}	V _{GS} = 18V	-	12	-	
Gate plateau voltage	V _(plateau)	V _{DD} = 400V, I _D = 4A	-	9.8	-	V

●Body diode electrical characteristics (Source-Drain) ($T_a = 25^\circ\text{C}$)

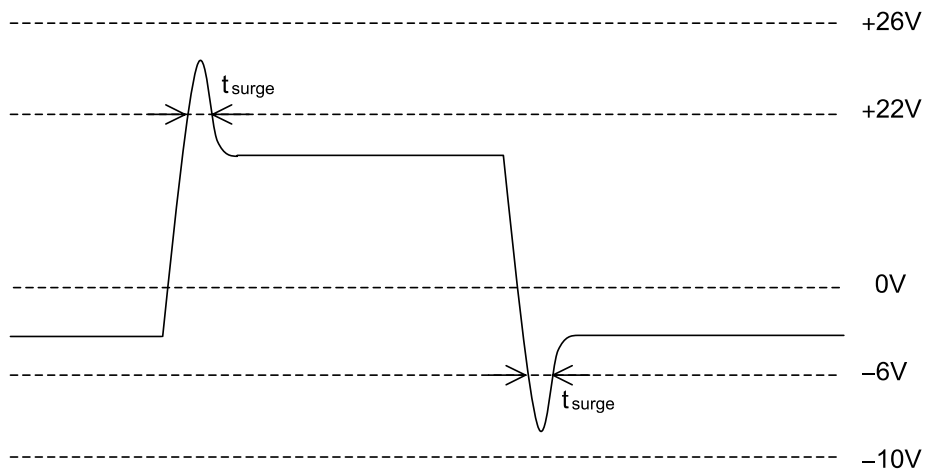
Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Inverse diode continuous, forward current	I_S^{*2}	$T_c = 25^\circ\text{C}$	-	-	14	A
Inverse diode direct current, pulsed	I_{SM}^{*3}		-	-	35	A
Forward voltage	V_{SD}^{*5}	$V_{GS} = 0\text{V}, I_S = 4\text{A}$	-	4.0	-	V
Reverse recovery time	t_{rr}^{*5}	$I_F = 4\text{A}, V_R = 400\text{V}$ $di/dt = 160\text{A}/\mu\text{s}$	-	22	-	ns
Reverse recovery charge	Q_{rr}^{*5}		-	21	-	nC
Peak reverse recovery current	I_{rrm}^{*5}		-	2.0	-	A

*1 Tolerances of dimensions and packing specifications slightly differ between TO-247 and TO-247N, which is unlikely to influence compatibility for mounting. Please refer to corresponding specifications of dimensions for more details.

*2 Limited only by maximum temperature allowed.

*3 $PW \leq 10\mu\text{s}$, Duty cycle $\leq 1\%$

*4 Example of acceptable V_{gs} waveform



*4 Pulsed

●Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

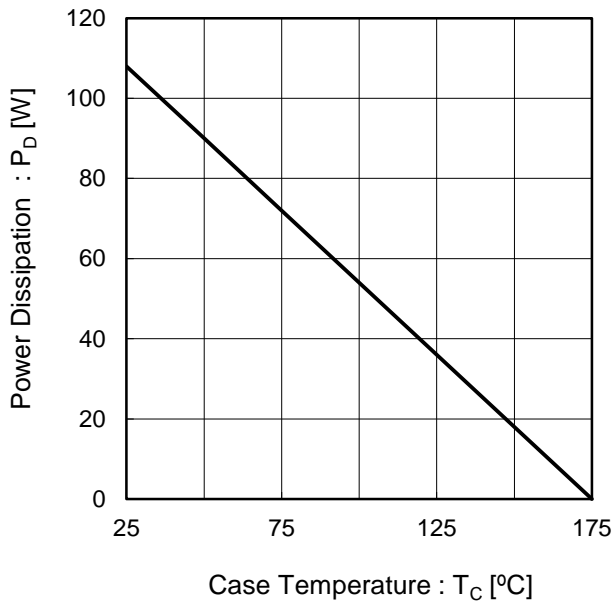


Fig.2 Maximum Safe Operating Area

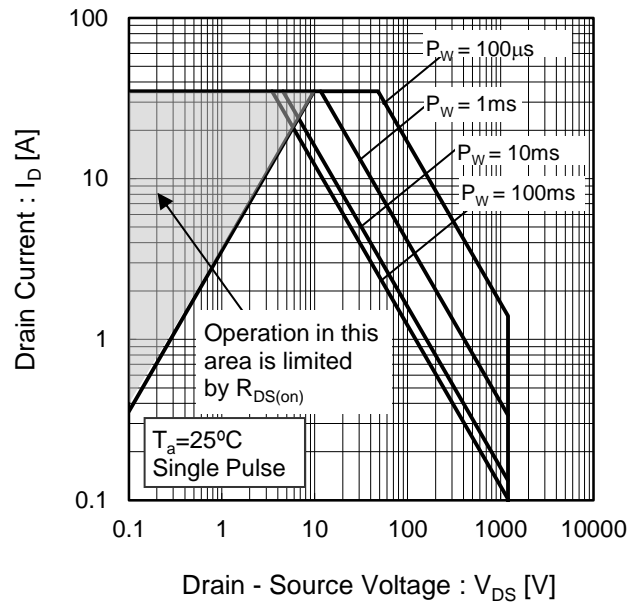
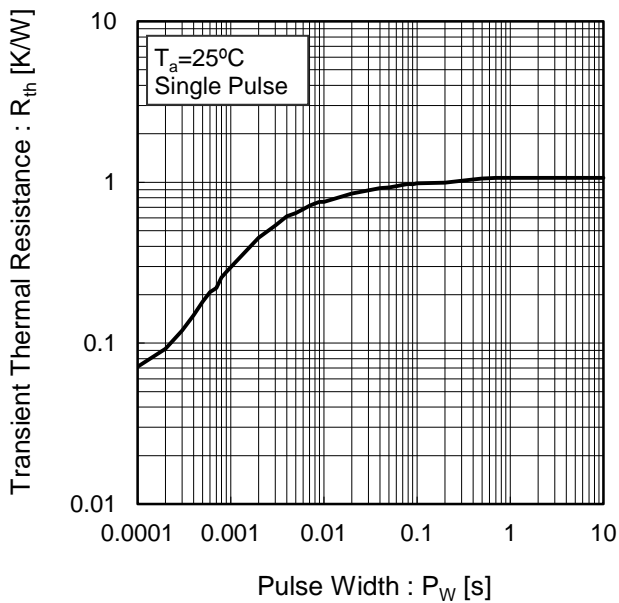


Fig.3 Typical Transient Thermal Resistance vs. Pulse Width



●Electrical characteristic curves

Fig.4 Typical Output Characteristics(I)

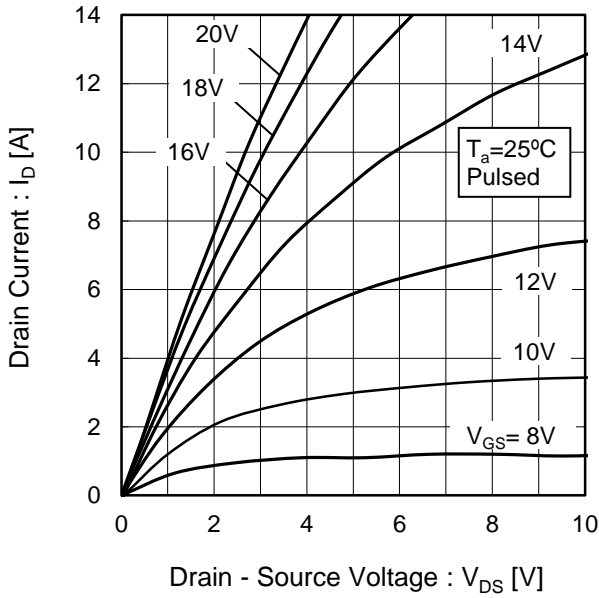


Fig.5 Typical Output Characteristics(II)

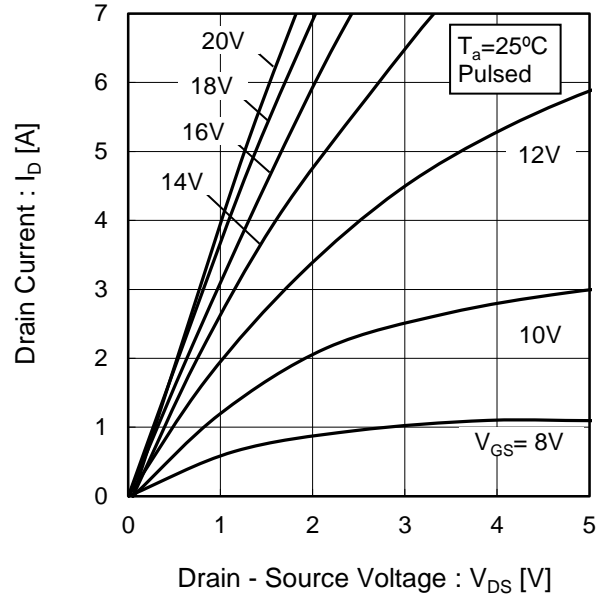


Fig.6 $T_j = 150^\circ\text{C}$ Typical Output Characteristics(I)

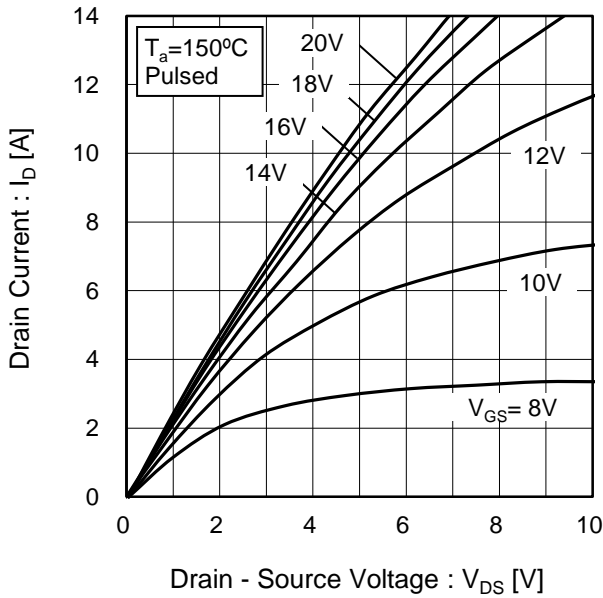
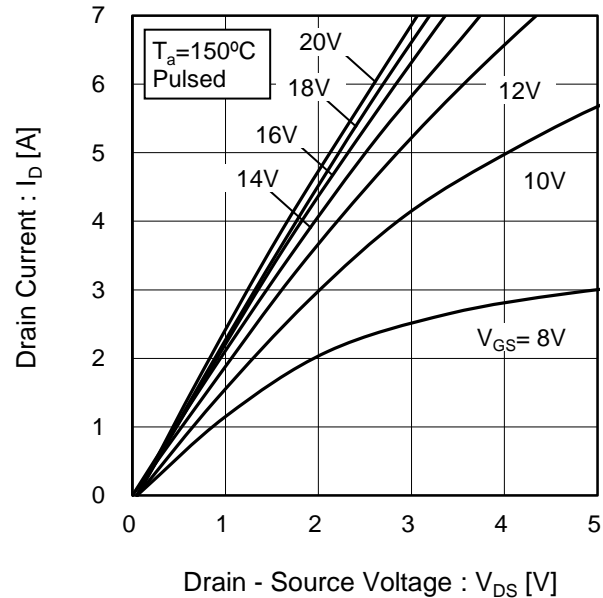


Fig.7 $T_j = 150^\circ\text{C}$ Typical Output Characteristics(II)



●Electrical characteristic curves

Fig.8 Typical Transfer Characteristics (I)

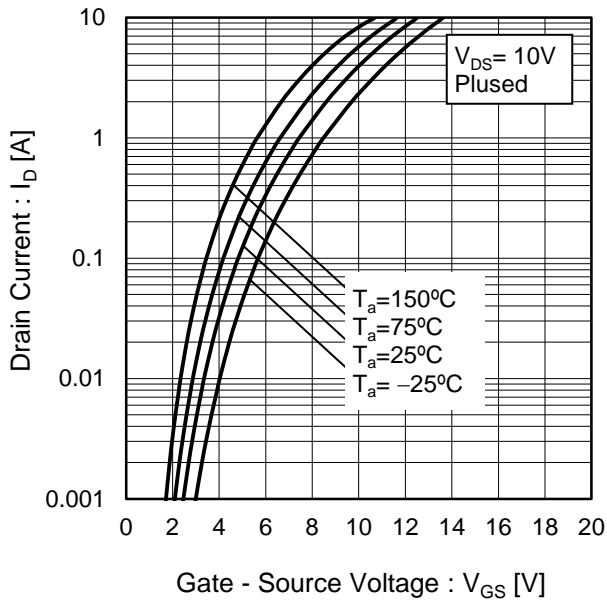


Fig.9 Typical Transfer Characteristics (II)

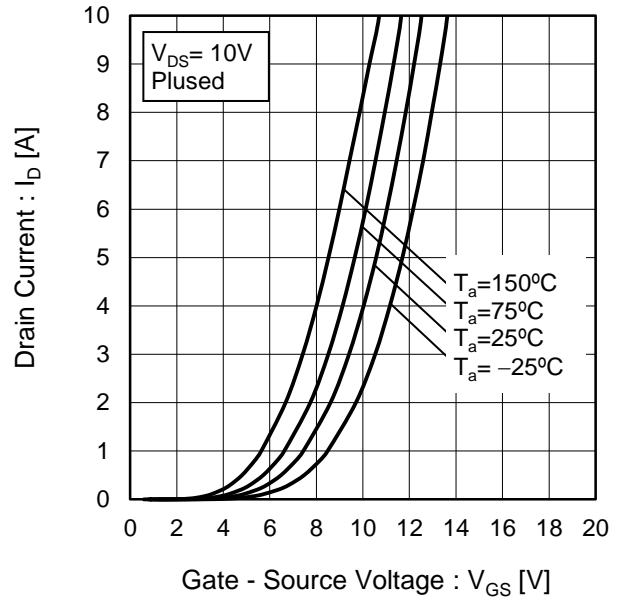


Fig.10 Gate Threshold Voltage vs. Junction Temperature

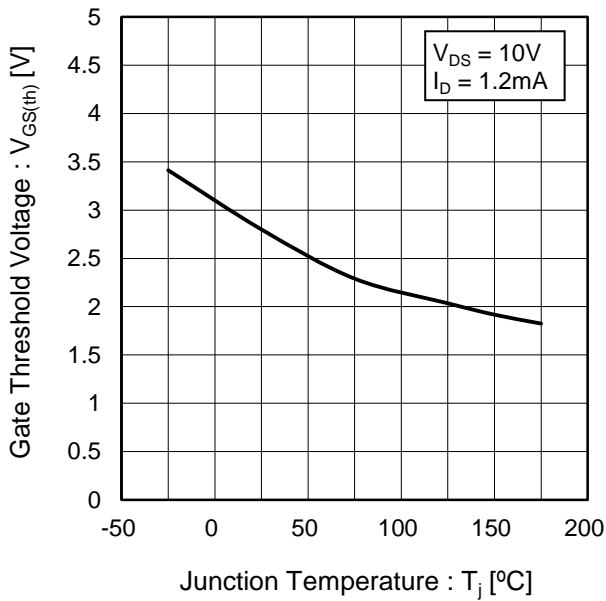
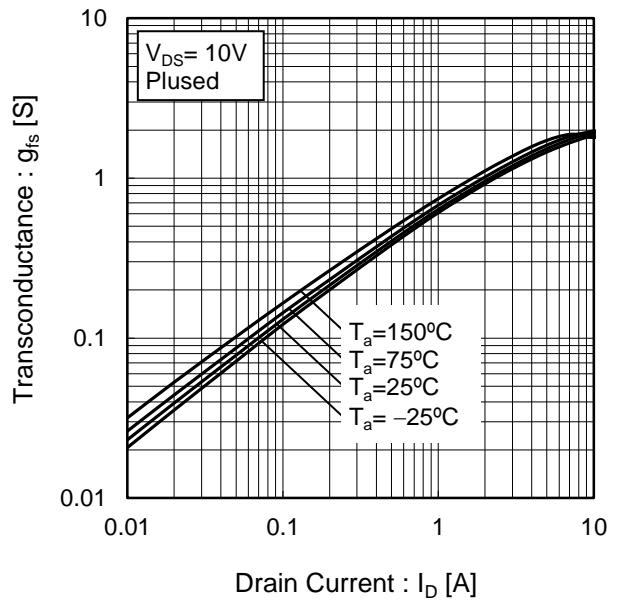


Fig.11 Transconductance vs. Drain Current



●Electrical characteristic curves

Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage

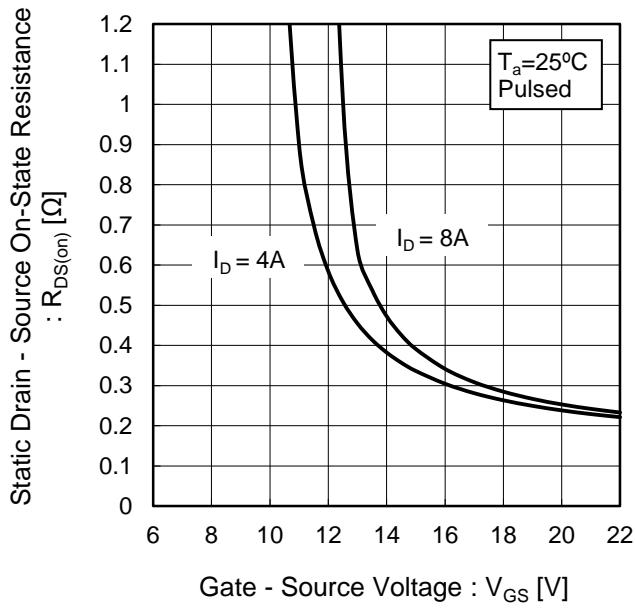


Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature

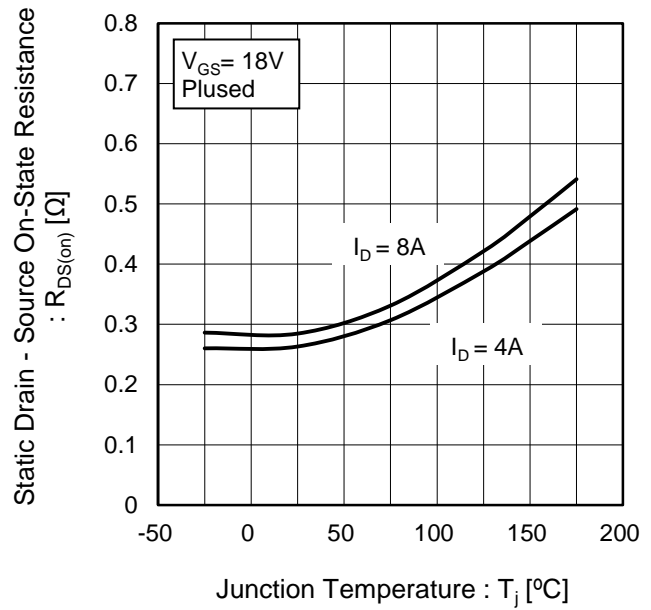
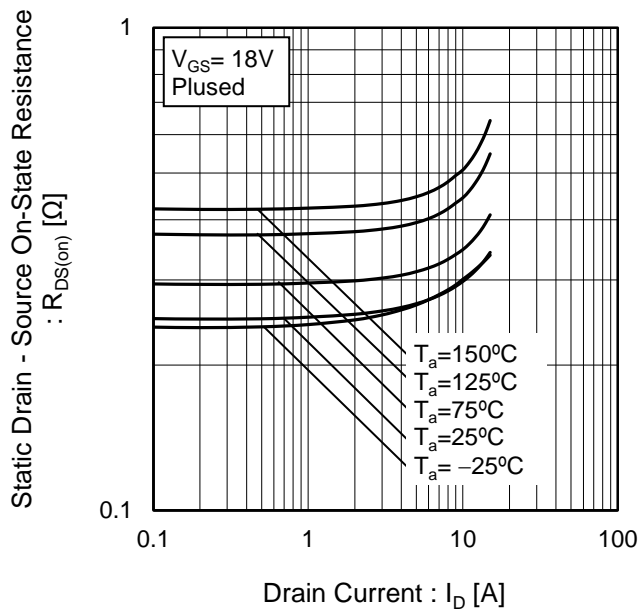


Fig.14 Static Drain - Source On - State Resistance vs. Drain Current



●Electrical characteristic curves

Fig.15 Typical Capacitance vs. Drain - Source Voltage

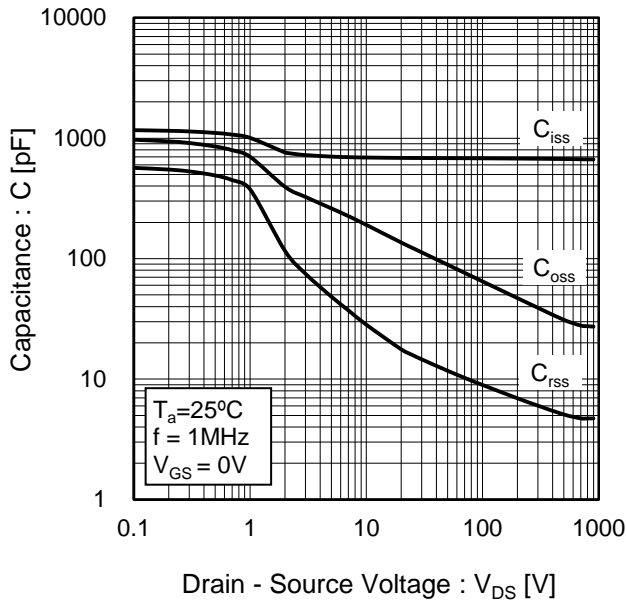


Fig.16 C_{OSS} Stored Energy

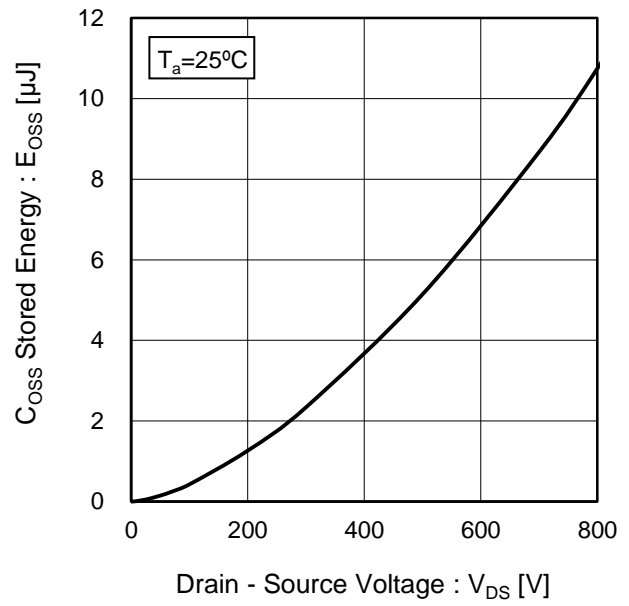


Fig.17 Switching Characteristics

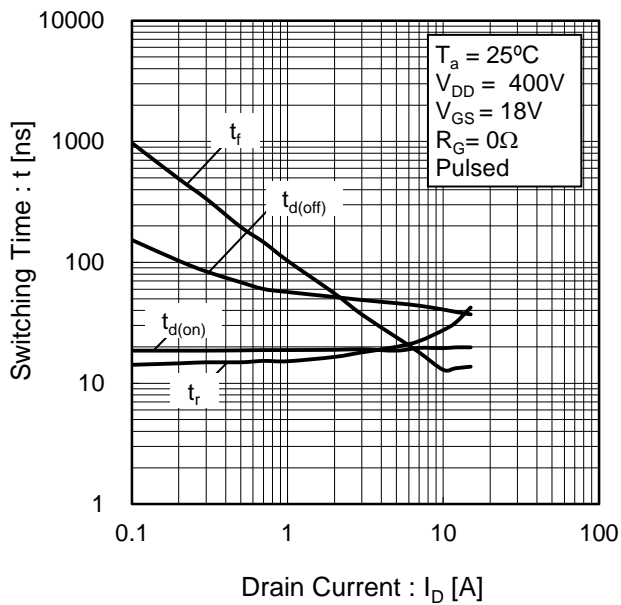
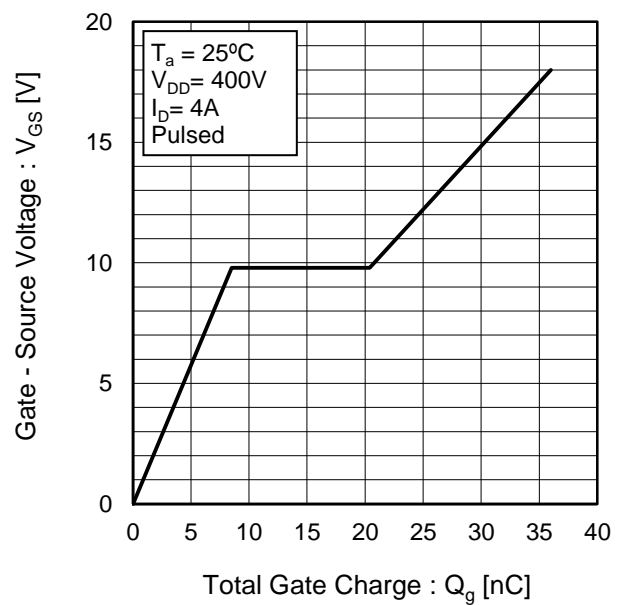


Fig.18 Dynamic Input Characteristics



●Electrical characteristic curves

Fig.19 Typical Switching Loss vs. Drain - Source Voltage

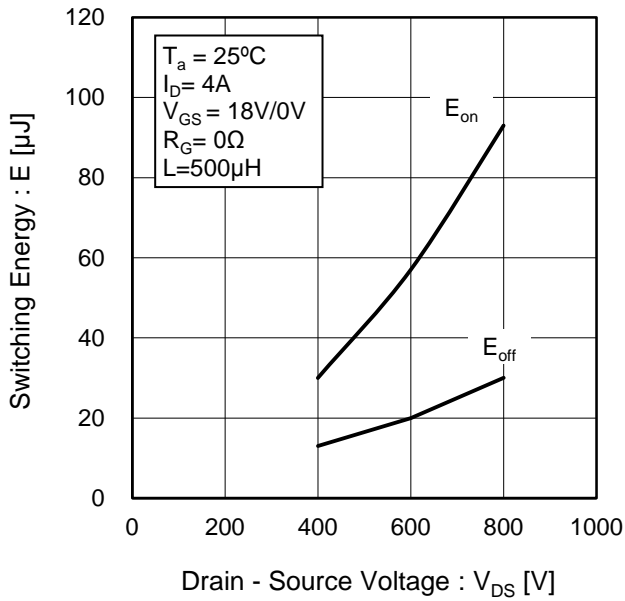


Fig.20 Typical Switching Loss vs. Drain Current

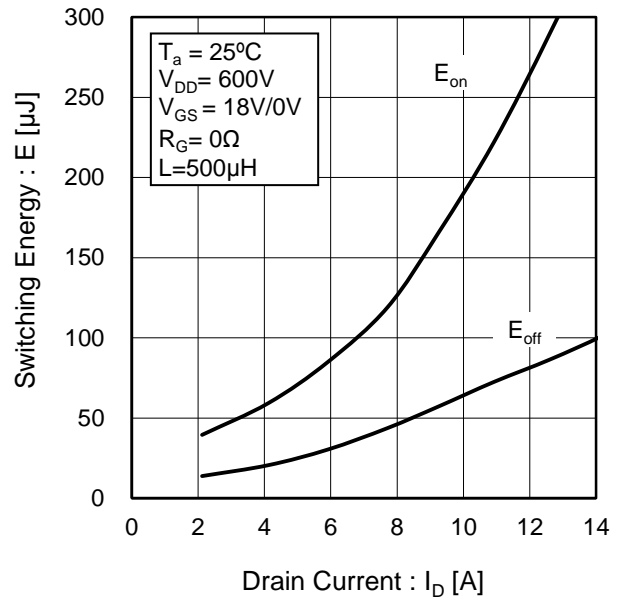
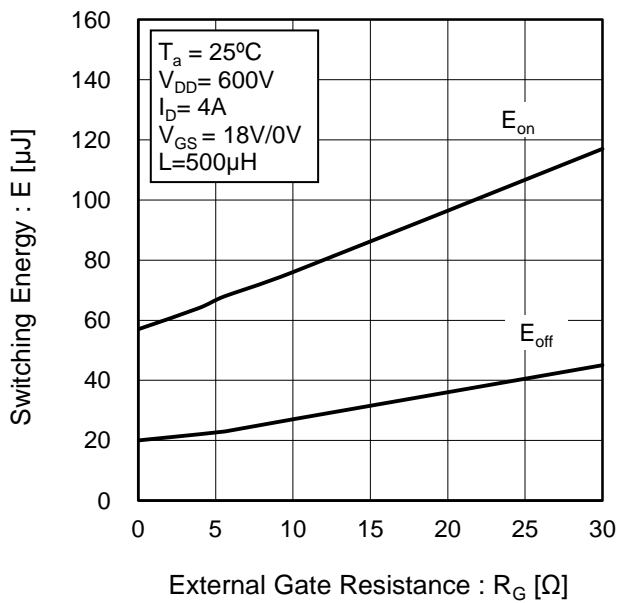


Fig.21 Typical Switching Loss vs. External Gate Resistance



●Electrical characteristic curves

Fig.22 Inverse Diode Forward Current vs. Source - Drain Voltage

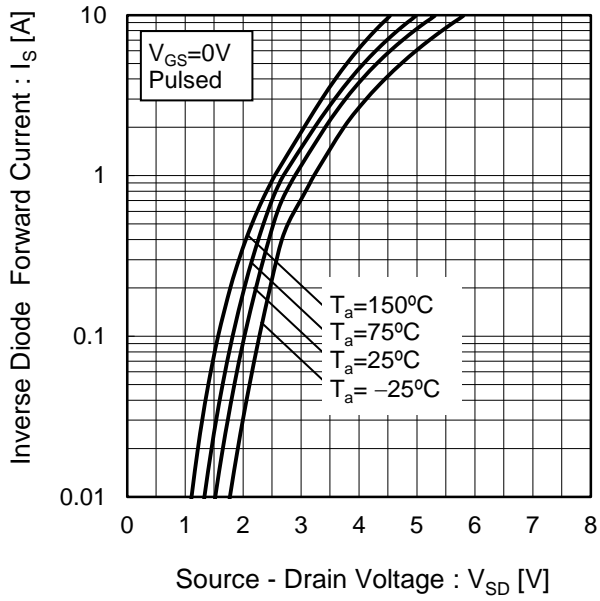
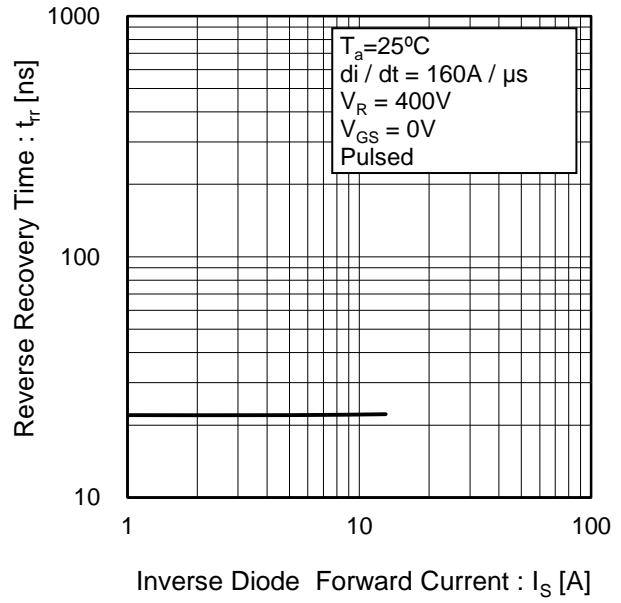


Fig.23 Reverse Recovery Time vs. Inverse Diode Forward Current



● Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

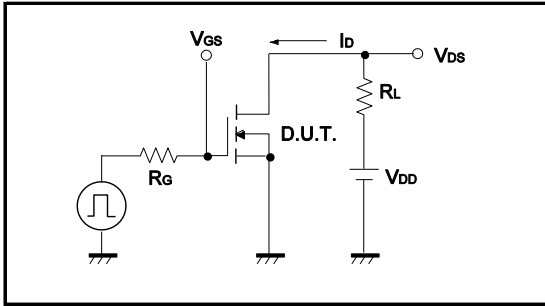


Fig.1-2 Switching Waveforms

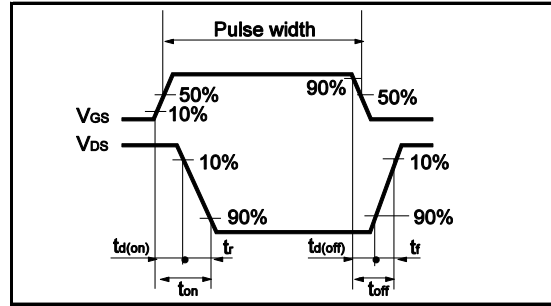


Fig.2-1 Gate Charge Measurement Circuit

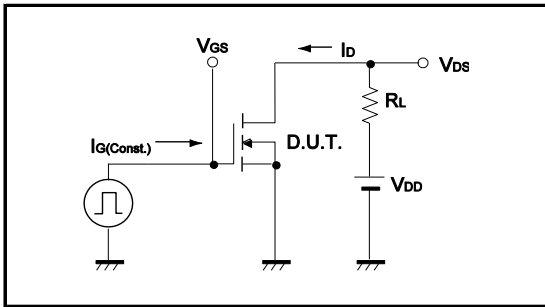


Fig.2-2 Gate Charge Waveform

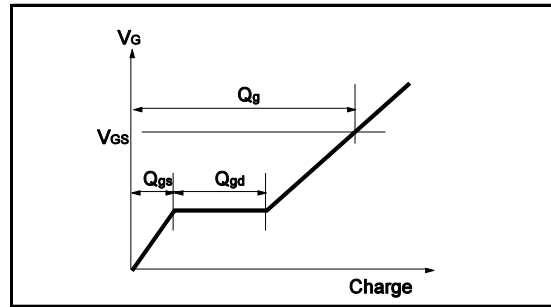


Fig.3-1 Switching Energy Measurement Circuit

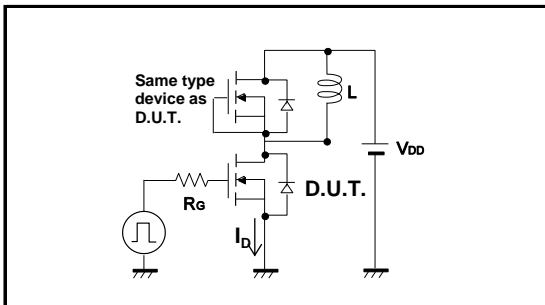


Fig.3-2 Switching Waveforms

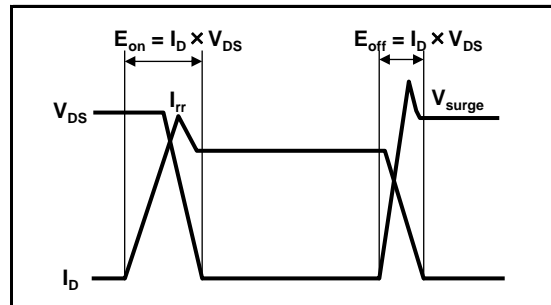


Fig.4-1 Reverse Recovery Time Measurement Circuit

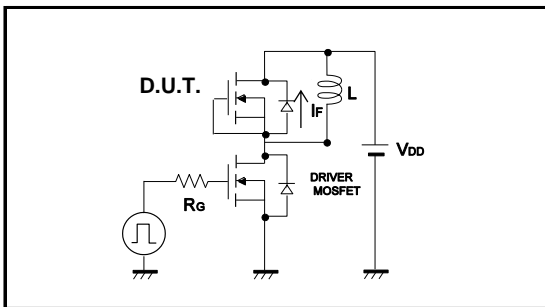
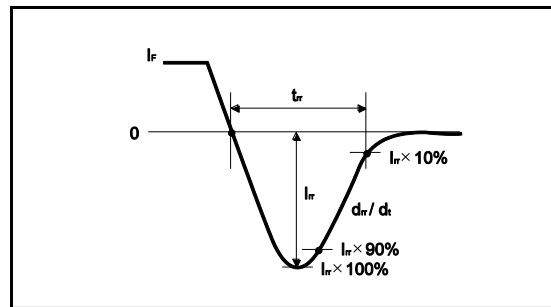


Fig.4-2 Reverse Recovery Waveform



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